

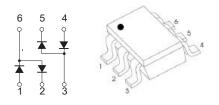


# Product data sheet

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SOT-363

# BAV99DW

SWITCHING DIODE

#### FEATURES

- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance

| ±<br> | = | +      |  |  |
|-------|---|--------|--|--|
| .KJG  |   |        |  |  |
| = +   | = | E<br>共 |  |  |

MAKING: KJG

#### Maximum Ratings @Ta=25℃

| Parameter   | Symbol   | Limit    | Unit |
|---|--|----------|------|
| Peak Repetitive Peak Reverse Voltage<br>Working Peak Reverse Voltage<br>DC Blocking Voltage | V <sub>RRM</sub><br>V <sub>RWM</sub><br>V <sub>R</sub> | 75       | V    |
| Forward Continuous Current  | I <sub>FM</sub>  | 300      | mA   |
| Average Rectified Output Current  | Ιο   | 150      | mA   |
| Non-Repetitive Peak Forward Surge Current @ t=8.3 ms  | I <sub>FSM</sub>                                       | 2.0      | А    |
| Power Dissipation   | PD   | 200      | mW   |
| Thermal Resistance Junction to Ambient  | $R_{	heta JA}$   | 625      | °C/W |
| Operating Junction Temperature  | TJ   | 150      | °C   |
| Storage Temperature   | T <sub>STG</sub>                                       | -55~+150 | °C   |

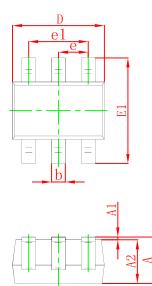
#### **ELECTRICAL CHARACTERISTICS(T**<sub>a</sub>=25℃ unless otherwise specified)

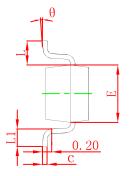
| Parameter   | Symbol   | Test conditions   | Min | Тур | Max   | Unit |
|---|--|---|-----|-----|-------|------|
| Reverse voltage V <sub>(BR)</sub>   |  | Ι <sub>R</sub> =2.5μΑ   | 75  |     |       | V    |
| Reverse current   | lr   | V <sub>R</sub> =75V   |     |     | 2.5   | μA   |
|   |  | VR=20V  |     |     | 25    | nA   |
| Forward voltage   | VF   | I⊧=1mA  |     |     | 0.715 | V    |
|   |  | I⊧=10mA   |     |     | 0.855 |      |
|   |  | l⊧=50mA   |     |     | 1     |      |
|   |  | I⊧=150mA  |     |     | 1.25  |      |
| Total capacitance   | Total capacitance C <sub>tot</sub> VR=0,f=1MHz |   |     |     | 2     | pF   |
| <b>Reverse recovery time</b> $t_{rr}$ $I_F = I_R = 10 \text{mA}, I_{rr} = 0.1 \times I_R, R_L = 10 \text{mA}$ |  | $I_F$ = $I_R$ =10mA, $I_{rr}$ =0.1× $I_R$ , $R_L$ =100 $\Omega$ |     |     | 4     | ns   |





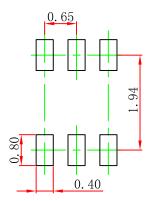
## SOT-363 Package Outline Dimensions





| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |  |
|--------|---------------------------|-------|----------------------|-------|--|
| Symbol | Min                       | Max   | Min                  | Max   |  |
| А      | 0.900                     | 1.100 | 0.035                | 0.043 |  |
| A1     | 0.000                     | 0.100 | 0.000                | 0.004 |  |
| A2     | 0.900                     | 1.000 | 0.035                | 0.039 |  |
| b      | 0.150                     | 0.350 | 0.006                | 0.014 |  |
| С      | 0.100                     | 0.150 | 0.004                | 0.006 |  |
| D      | 2.000                     | 2.200 | 0.079                | 0.087 |  |
| E      | 1.150                     | 1.350 | 0.045                | 0.053 |  |
| E1     | 2.150                     | 2.400 | 0.085 0.094          |       |  |
| e      | 0.650 TYP                 |       | 0.026                | 6 TYP |  |
| e1     | 1.200                     | 1.400 | 0.047                | 0.055 |  |
| L      | 0.525 REF                 |       | 0.021 REF            |       |  |
| L1     | 0.260                     | 0.460 | 0.010                | 0.018 |  |
| θ      | 0°                        | 8°    | 0°                   | 8°    |  |

## SOT-363 Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:±0.05mm.

3. The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

| P/N     | PKG     | QTY  |
|---------|---------|------|
| BAV99DW | SOT-363 | 3000 |
|         |         |      |





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